

## PNT723T503E0-2

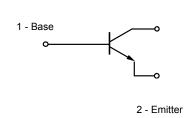
3 - Collector

# High EB High DC gain Ultra-Small package switch transistor

#### Feature

This device is Pb-Free, Halogen Free/BFR Free and RoHS compliant.

- > Package: SOT-723
- Emitter -Base Breakdown Voltage 11V
- > High DC current gain typical 380
- Low Saturation Voltage 80mv
- > 0.15 continuous collector current
- NPN switch transistor



## **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness:≤3mil

## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Value	Units
Collector-Emitter Breakdown Voltage	V (BR)CEO	50	V
Collector-Base Breakdown Voltage	V (BR)CBO	80	V
Emitter -Base Breakdown Voltage	V <sub>(BR)EBO</sub>	11	V
Collector Current	Ι <sub>C</sub>	0.15	А
Total Dissipation @25°C	P <sub>tot</sub>	0.15	W
Storage Temperature	T <sub>stg</sub>	-65~150	°C
Max. Operating Junction Temperature	Tj	150	°C

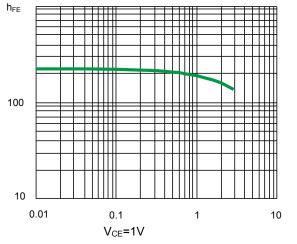
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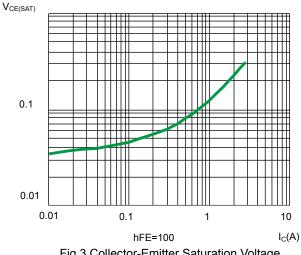
## Absolute maximum rating@25°C

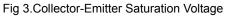
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =50uA	80			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA	50			V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =50uA		11		V
Collector Cut-off Current (I <sub>E</sub> =0)	I <sub>CBO</sub>	V <sub>CB</sub> =60V			0.1	μA
Emitter Cut-off Current(I <sub>C</sub> =0)	I <sub>EBO</sub>	V <sub>EB</sub> =7V			0.1	μA
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> =1mA,V <sub>CE</sub> =6V	250		560	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I <sub>C</sub> =50mA,I <sub>B</sub> =5mA	-	0.08		V
Transition frequency	f⊤	V <sub>CE</sub> =12V,I <sub>E</sub> =-2mA,f=100MHz		200		MHz
Output Capacitance	Cob	V <sub>CE</sub> =12V,I <sub>E</sub> =0mA,f=1MHz		2	3.5	pF

## **Typical Characteristics**









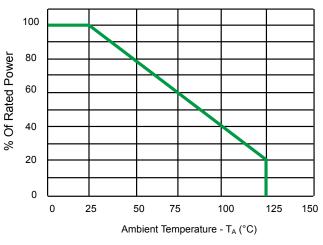
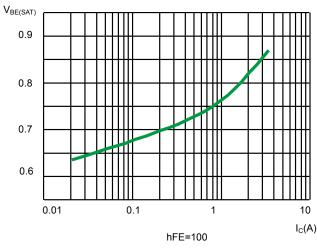


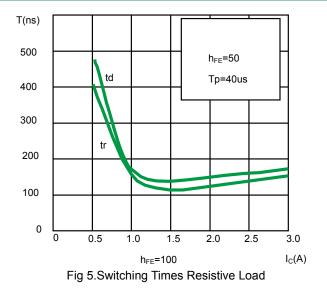
Fig2. Power Derating Curve

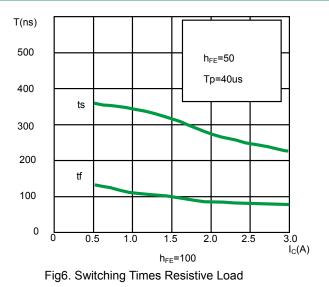




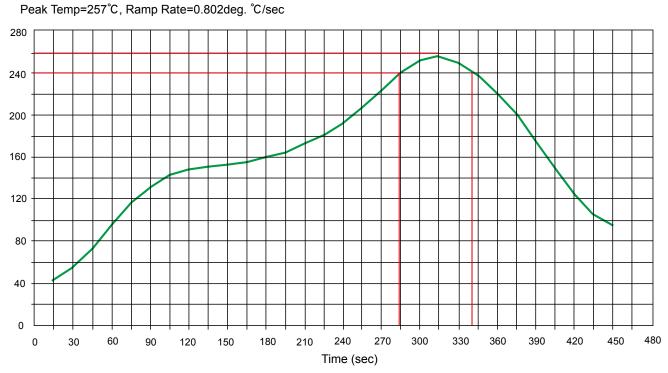
# High EB High DC gain Ultra-Small package switch transistor P

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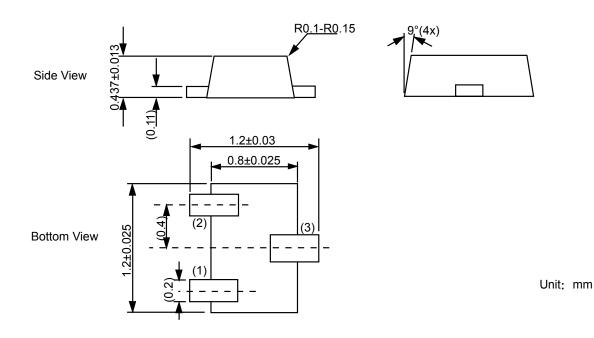


### **Solder Reflow Recommendation**



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## **Product dimension (SOT-723)**



Unit: mm

# Ordering information

Device	Package	Shipping
PNT723T503E0-2	SOT-723 (Pb-Free)	10000 / Tape & Reel

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